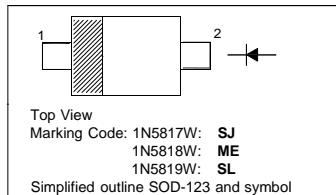


1A Surface Mount Schottky Barrier Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage 1N5817W 1N5818W 1N5819W	V_R	20	V
		30	
		40	
Average Forward Rectified Current	$I_{F(AV)}$	1	A
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine-Wave)	I_{FSM}	9	A
Power Dissipation	P_{tot}	450	mW
Operating Temperature Range	T_j	- 55 to + 125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

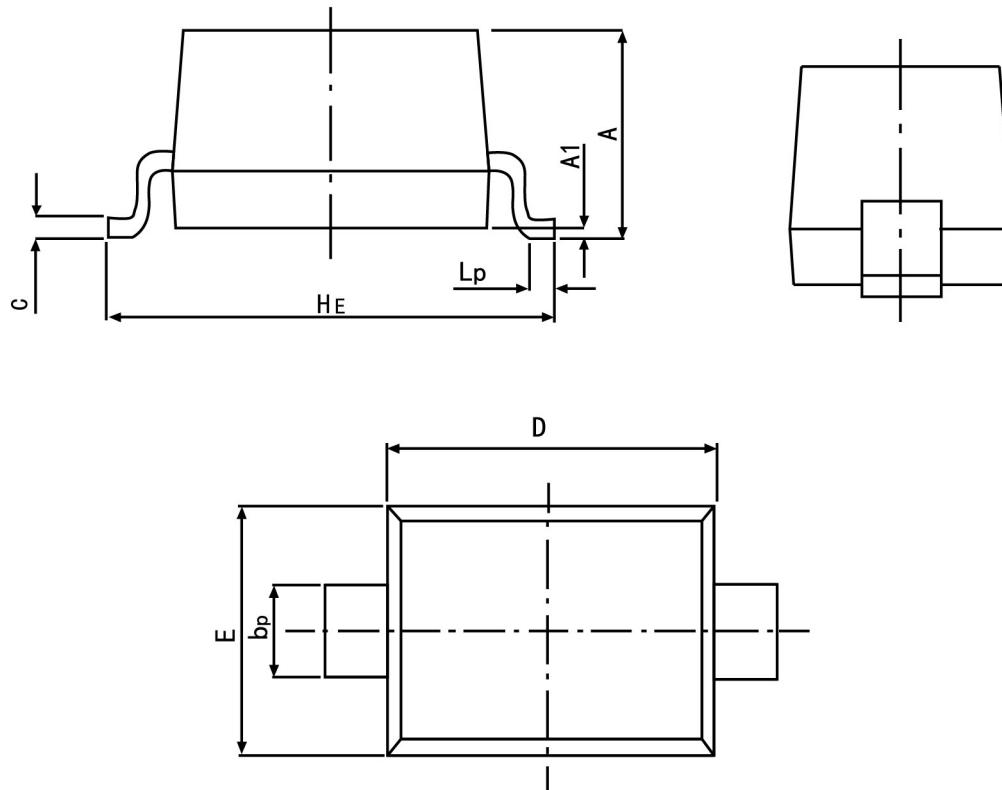
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 1 \text{ mA}$ 1N5817W 1N5818W 1N5819W	$V_{(BR)R}$	20	-	V
		30	-	
		40	-	
Reverse Current at $V_R = 20 \text{ V}$ 1N5817W at $V_R = 30 \text{ V}$ 1N5818W at $V_R = 40 \text{ V}$ 1N5819W at $V_R = 4 \text{ V}$ 1N5819W at $V_R = 6 \text{ V}$ 1N5819W	I_R	-	1	mA
		-	1	
		-	1	
		-	0.05	
		-	0.075	
Forward Voltage at $I_F = 0.1 \text{ A}$ 1N5819W at $I_F = 1 \text{ A}$ 1N5817W 1N5818W 1N5819W at $I_F = 3 \text{ A}$ 1N5817W 1N5818W 1N5819W	V_F	-	0.45	V
		-	0.45	
		-	0.55	
		-	0.6	
		-	0.75	
		-	0.875	
		-	0.9	
Total Capacitance at $V_R = 4 \text{ V}, f = 1 \text{ MHz}$	C_{tot}	-	120	pF

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.20
bp	0.50	0.60
C	0.100	0.135
D	2.55	2.75
E	1.55	1.65
HE	3.55	3.85
A1	0.01	0.10
Lp	0.20	0.50